ABSTRACT

In order to provide light emitting devices which have simple constructions and thus can be fabricated easily, and can stably provide high light emission efficiencies for a long time period, a light emitting device includes an n-type nitride semiconductor layer (2) at a first main surface side of a nitride semiconductor substrate (1), a p-type nitride semiconductor layer (6) placed more distantly from the nitride semiconductor substrate than the n-type nitride semiconductor layer at the first main surface side and a light emitting layer (4) placed between the n-type nitride semiconductor layer and the p-type nitride semiconductor layer (6) at the first main surface side. The nitride semiconductor substrate has a resistivity of 0.5 Ω•cm or less and the p-type nitride semiconductor layer side is down-mounted so that light is emitted from the second main surface (1a) of the nitride semiconductor substrate at the opposite side from the first main surface.